

NTBG025N065SC1

Silicon Carbide (SiC) MOSFET - 19 mohm, 650 V, M2, D2PAK-7L

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

- High Junction Temperature ($T_j = 175^\circ\text{C}$)
 - Kelvin Source Configuration
 - Ultra Low Gate Charge ($Q_g(\text{tot}) = 164 \text{ nC}$)
 - Low Output Capacitance ($C_{oss} = 278 \text{ pF}$)
 - Zero reverse recovery current of body diode
 - Higher system reliability
 - Low gate noise and switching loss
 - Low switching loss
 - Low switching loss
 - Higher system reliability in LLC and Phase shift full bridge circuit
 - 650V rated
 - 100% Avalanche Tested
 - Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
 - Moisture Sensitivity Level 1 guarantee
 - Internal Gate Resistance: 1.5Ω
- For more features, see the data sheet

- Telecommunication
- Cloud system
- Industrial
- Telecom power
- Server power
- UPS / ESS
- Solar

	Pricing (\$/Unit)	Compliance	Status	Family	Blocking Voltage BV_{DSS} (V)	$I_{D(\text{max})}$ (A)	$R_{DS(\text{on})}$ Typ @ 25°C (m Ω)	Q_g Total (nC)	Output Capacitance (pF)	T_j Max ($^\circ\text{C}$)	Package Type
NTBG025N065SC1	13.813		NEW	M2	650	106	19	164	278	175	D2PAK7 (TO-263-7L HV)